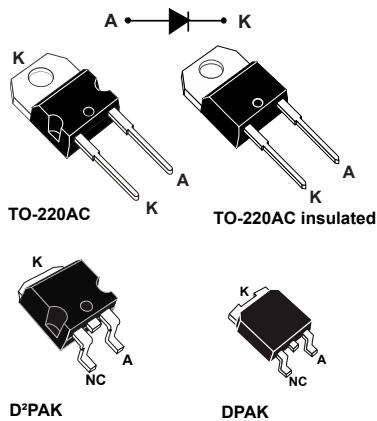


650 V, 8 A high surge silicon carbide power Schottky diode



Features

- No reverse recovery charge in application current range
- Switching behavior independent of temperature
- High forward surge capability
- Insulated package TO-220AC Ins:
 - Insulated voltage: 2500 V_{RMS}
 - Typical package capacitance: 7 pF
- Power efficient product

Applications

- Switch mode power supply
- PFC
- DCDC converters
- LLC topologies
- Boost diode

Description

This 8 A, 650 V SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

This [STPSC8H065](#) is especially suited for use in PFC applications. This ST SiC diode will boost the performance in hard switching conditions. Its high forward surge capability ensures a good robustness during transient phases.

Product status

[STPSC8H065](#)

Product summary

Symbol	Value
$I_{F(AV)}$	8 A
V_{RRM}	650 V
$T_{j(max.)}$	175 °C

Product label



1 Characteristics

Table 1. Absolute ratings (limiting values at 25 °C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		650	V
$I_{F(RMS)}$	Forward rms current		22	A
$I_{F(AV)}$	Average forward current	TO-220AC, DPAK, D ² PAK, $T_c = 140\text{ °C}^{(1)}$, DC	8	A
		TO-220AC Ins, $T_c = 95\text{ °C}^{(1)}$		
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal, $T_c = 25\text{ °C}$	75	A
		$t_p = 10\text{ ms}$ sinusoidal, $T_c = 125\text{ °C}$	69	
		$t_p = 10\text{ }\mu\text{s}$ square, $T_c = 25\text{ °C}$	420	
I_{FRM}	Repetitive peak forward current	TO-220AC, DPAK, D ² PAK, $T_c = 140\text{ °C}^{(1)}$, $T_j = 175\text{ °C}$, $\delta = 0.1$	33	A
		TO-220AC Ins, $T_c = 95\text{ °C}^{(1)}$, $T_j = 175\text{ °C}$, $\delta = 0.1$		
T_{stg}	Storage temperature range		-55 to +175	°C
T_j	Operating junction temperature range ⁽²⁾		-40 to +175	°C

1. Value based on $R_{th(j-c)}$ max.

2. $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter		Typ. value	Max. value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AC, DPAK, D ² PAK	1.3	1.6	°C/W
		TO-220AC Ins	2.45	3.8	

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-	7	80	μA
		$T_j = 150\text{ °C}$		-	65	335	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 8\text{ A}$	-	1.56	1.75	V
		$T_j = 150\text{ °C}$		-	1.98	2.50	

1. $t_p = 10\text{ ms}$, $\delta < 2\%$

2. $t_p = 500\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 1.35 \times I_{F(AV)} + 0.144 \times I_{F(RMS)}^2$$

For more information, please refer to the following application notes related to the power losses :

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

Table 4. Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Typ.	Unit
Q_{cj}	Total capacitive charge	$V_R = 400 \text{ V}$	23.5	nC
C_j	Total capacitance	$V_R = 0 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	414	pF
		$V_R = 400 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	38	

1. Most accurate value for the capacitive charge: $Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$

1.1 Characteristics (curves)

Figure 1. Forward voltage drop versus forward current (typical values, low level)

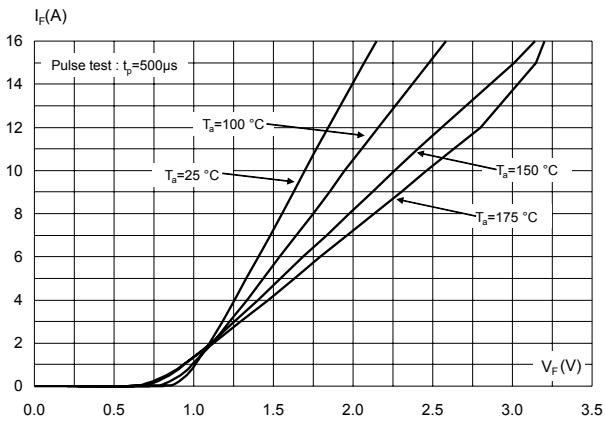


Figure 2. Forward voltage drop versus forward current (typical values, high level)

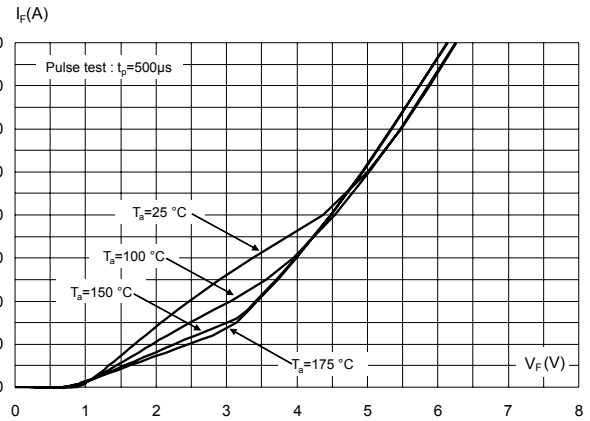


Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

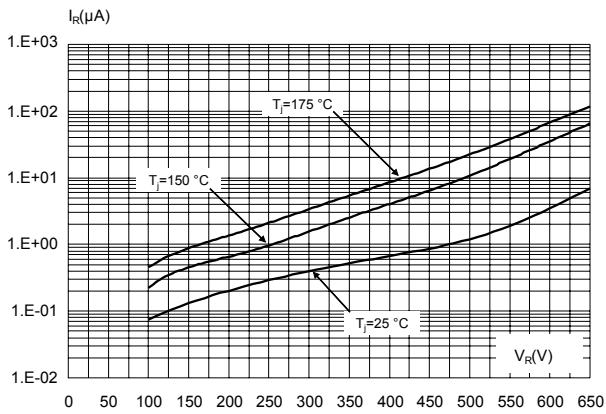


Figure 4. Peak forward current versus case temperature (TO-220AC, DPAK, D²PAK)

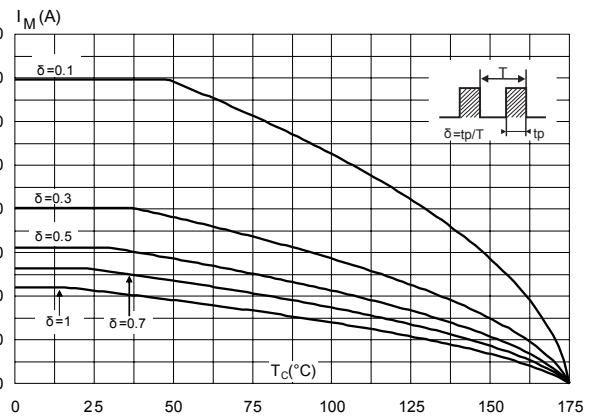


Figure 5. Peak forward current versus case temperature (TO-220AC Ins)

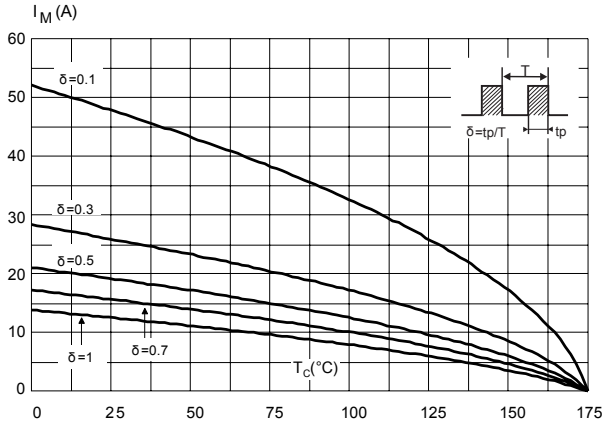


Figure 6. Junction capacitance versus reverse voltage applied (typical values)

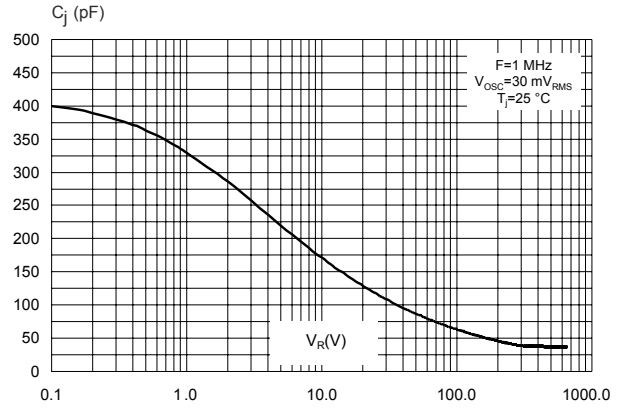


Figure 7. Relative variation of thermal impedance junction to case versus pulse duration (TO-220AC, DPAK and D²PAK)

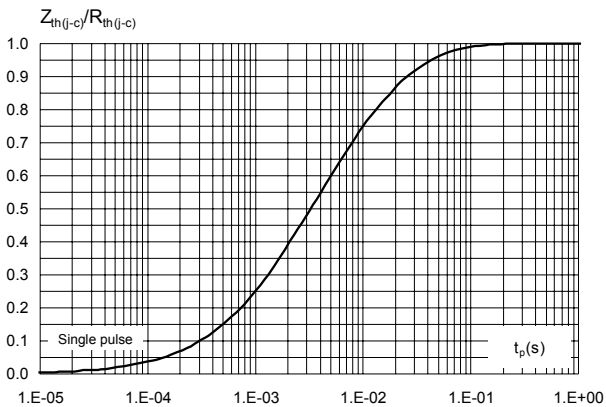


Figure 8. Relative variation of thermal impedance junction to case versus pulse duration (TO-220AC Ins)

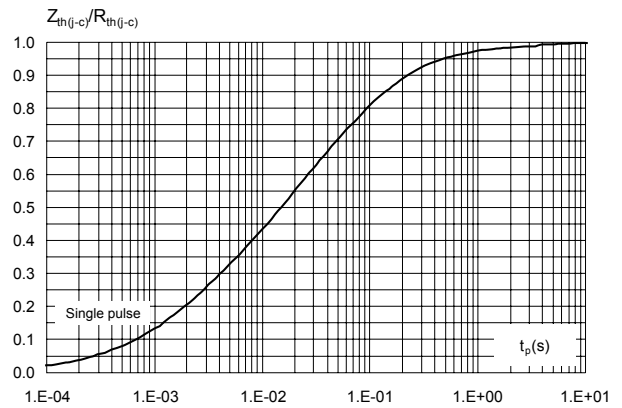


Figure 9. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

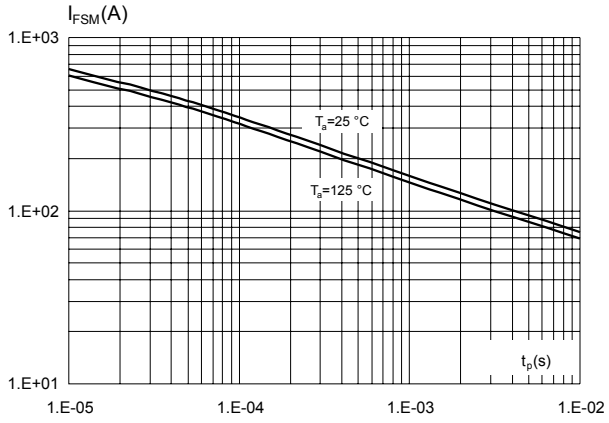
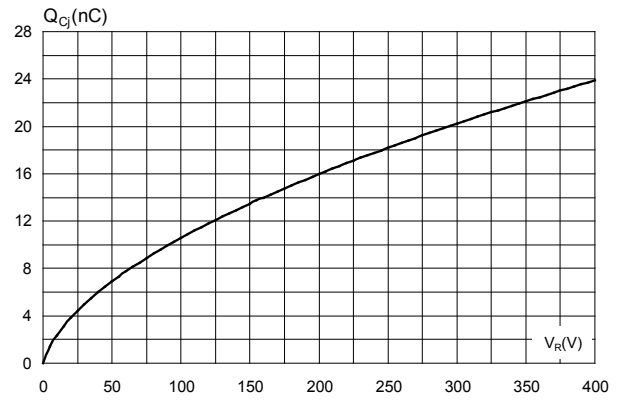


Figure 10. Total capacitive charges versus reverse voltage applied (typical values)



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 DPAK package information

- Epoxy meets UL94, V0

Figure 11. DPAK package outline

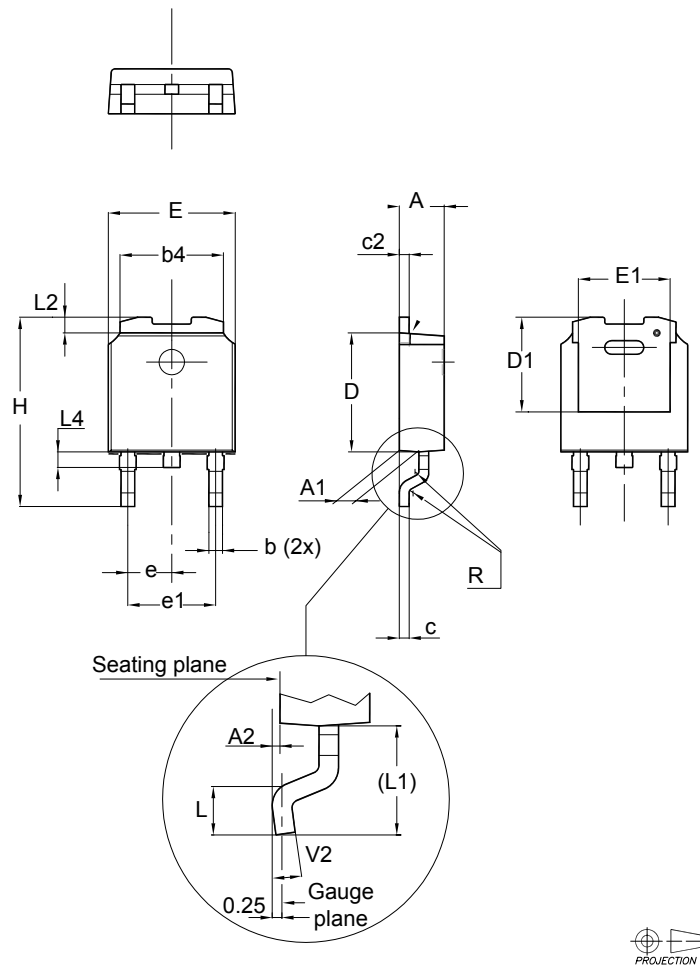
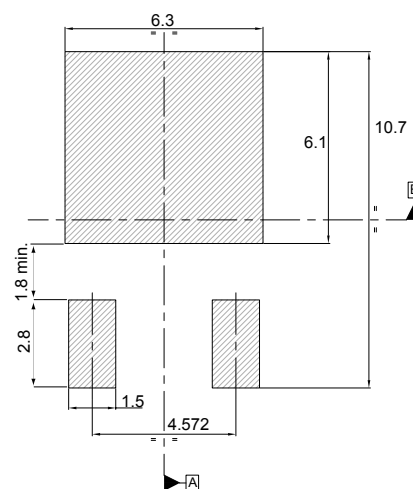


Table 5. DPAK mechanical data

Dim.	Dimensions					
	Millimeters			Inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
b	0.64		0.90	0.025		0.035
b4	5.20		5.40	0.205		0.213
c	0.45		0.60	0.018		0.024
c2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
D1	4.95	5.10	5.25	0.195	0.201	0.207
E	6.40		6.60	0.252		0.260
E1	4.60	4.70	4.80	0.181	0.185	0.189
e	2.159	2.286	2.413	0.085	0.090	0.095
e1	4.445	4.572	4.699	0.175	0.180	0.185
H	9.35		10.10	0.368		0.398
L	1.00		1.50	0.039		0.059
(L1)	2.60	2.80	3.00	0.102	0.110	0.118
L2	0.65	0.80	0.95	0.026	0.031	0.037
L4	0.60		1.00	0.024		0.039
R		0.20			0.008	
V2	0°		8°	0°		8°

1. Inches dimensions given for reference only

Figure 12. DPAK recommended footprint (dimensions are in mm)

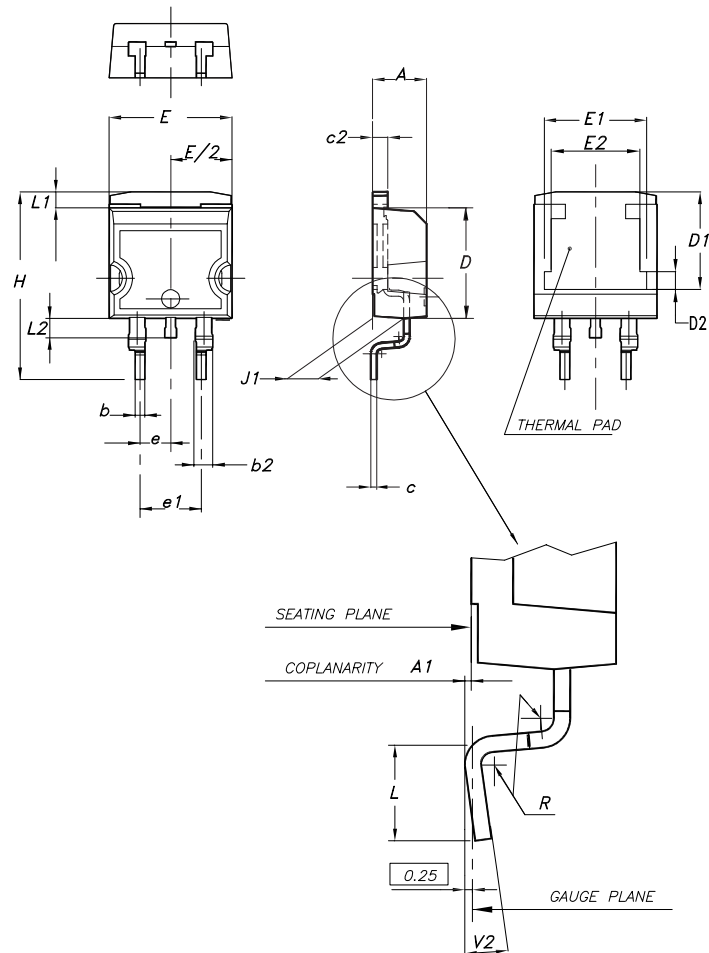


The device must be positioned within $\Phi 0.05 \text{ A B}$

2.2 D²PAK package information

- Epoxy meets UL94, V0.
- Cooling method: by conduction (C)

Figure 13. D²PAK package outline

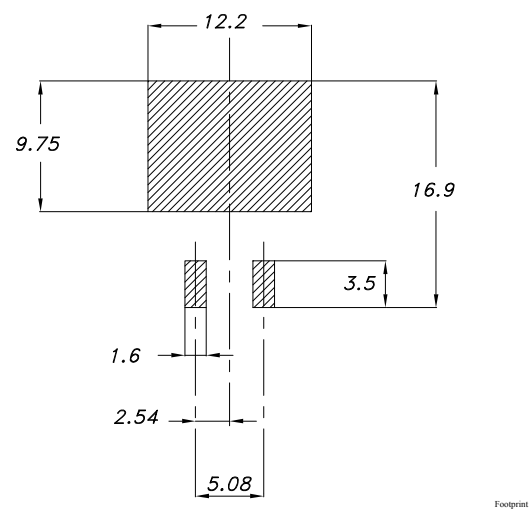


Note: This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Table 6. D²PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches (for reference only)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.028		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.018		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50	7.75	8.00	0.295	0.305	0.315
D2	1.10	1.30	1.50	0.043	0.051	0.060
E	10.00		10.40	0.394		0.409
E1	8.30	8.50	8.70	0.335	0.343	0.346
E2	6.85	7.05	7.25	0.266	0.278	0.282
e		2.54			0.100	
e1	4.88		5.28	0.190		0.205
H	15.00		15.85	0.591		0.624
J1	2.49		2.69	0.097		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.049		0.055
L2	1.30		1.75	0.050		0.069
R		0.40			0.015	
V2	0°		8°	0°		8°

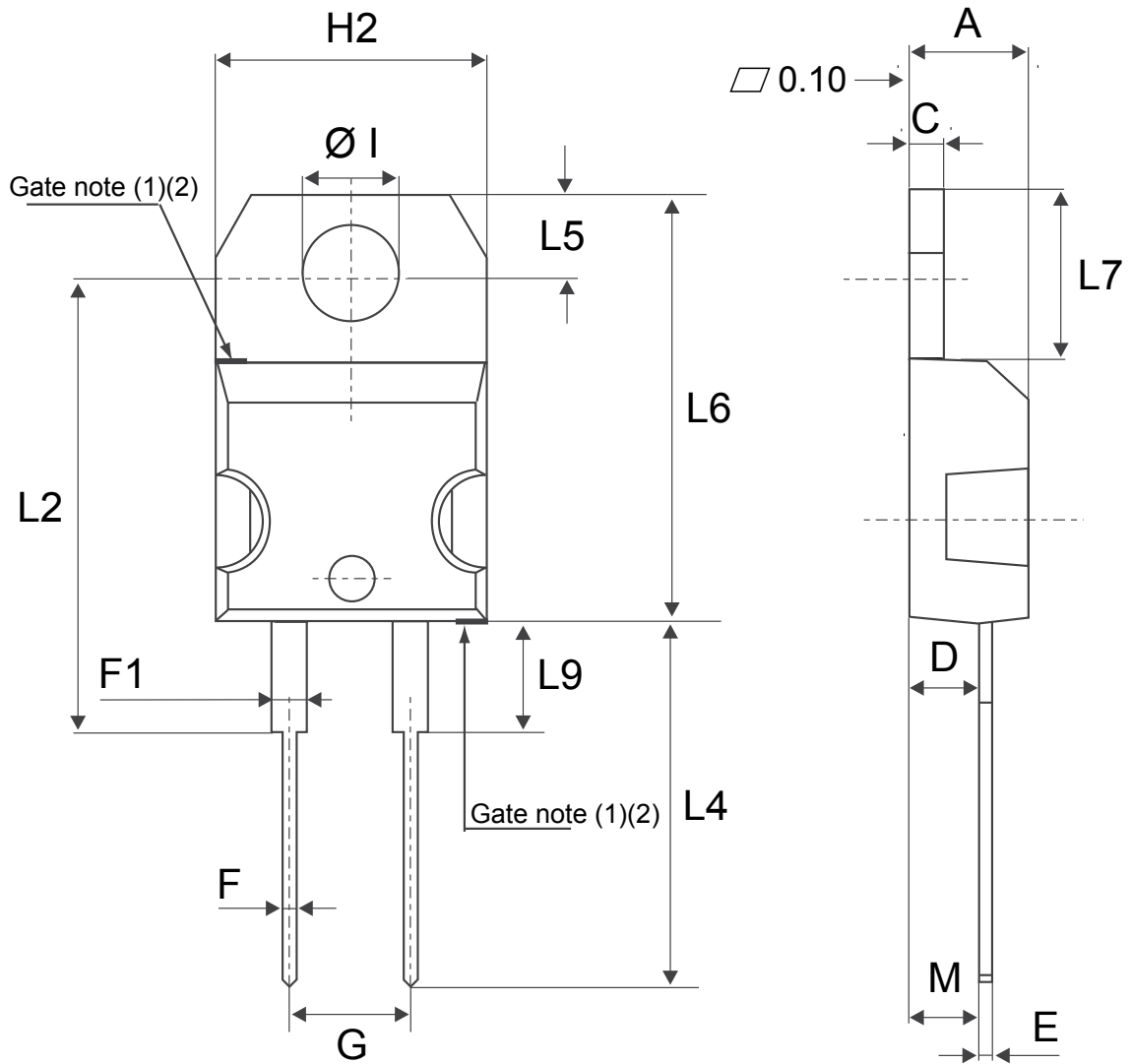
Figure 14. D²PAK recommended footprint (dimensions are in mm)



2.3 TO-220AC package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m

Figure 15. TO-220AC package outline



(1) :Max resin gate protusion 0.5 mm

(2) :Resin gate position is accepted in each of the two positions shown on the drawings or their symmetrical

Table 7. TO-220AC package mechanical data

Ref.	Dimensions			
	Millimeters		Inches (for reference only)	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.60 typ.		0.102 typ.	
Diam	3.75	3.85	0.147	0.151

2.4 TO-220AC Ins package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m

Figure 16. TO-220AC Ins package outline

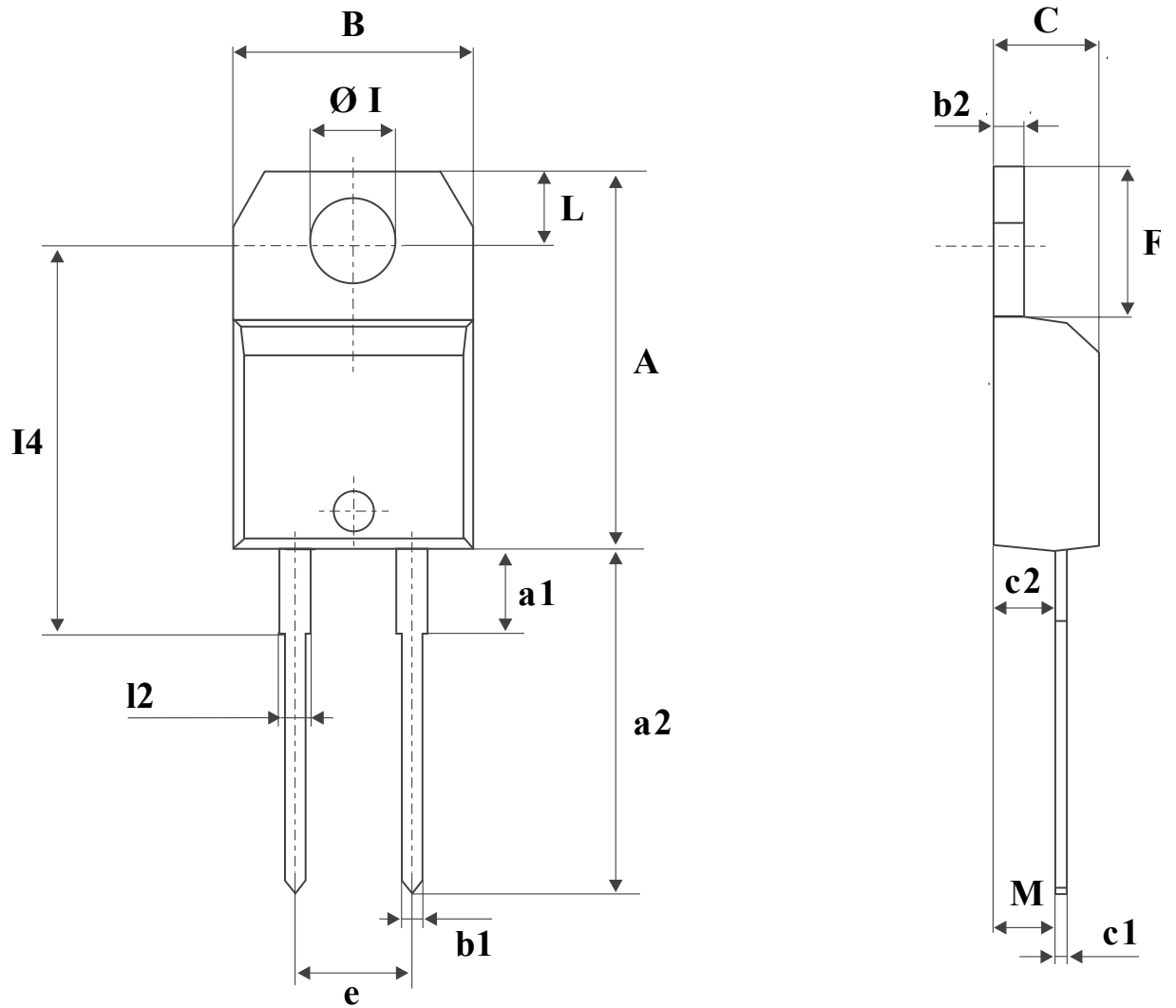


Table 8. TO-220AC Ins package mechanical data

Ref.	Dimensions					
	Millimeters			Inches (for reference only)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	4.80		5.40	0.189		0.212
F	6.20		6.60	0.244		0.259
L	2.65		2.95	0.104		0.116
l2	1.14		1.70	0.044		0.066
l4	15.80	16.40	16.80	0.622	0.645	0.661
M		2.60			0.102	
Øl	3.75		3.85	0.147		0.151

3 Ordering Information

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC8H065D	STPSC8H065D	TO-220AC	1.86 g	50	Tube
STPSC8H065DI	STPSC 8H065DI	TO-220AC Ins	2.12 g	50	Tube
STPSC8H065G-TR	STPSC8H065G	D ² PAK	1.48 g	1000	Tape and reel
STPSC8H065B-TR	STPSC 8H065	DPAK	0.32 g	2500	Tape and reel

Revision history

Table 10. Document revision history

Date	Version	Changes
31-Aug-2012	1	First issue.
10-Oct-2012	2	Added Max. value to Table 3.
07-Nov-2013	3	Updated Figure 1, Figure 2, Figure 13, Figure 14, and Table 9.
07-Jan-2014	4	Added TO-220AC Ins package.
21-Jul-2015	5	Updated Table 10 and reformatted to current standard.
22-Feb-2016	6	Updated cover image.
05-Feb-2019	7	Updated D ² PAK package information. Added Section Applications and Section Sustainable technology program .

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Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331